





IFN152 N-Channel JFET

Features

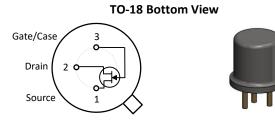
- InterFET <u>N0132L Geometry</u>
- Low Noise: 1.0 nV/VHz Typical
- High Gain: 30mS Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

Applications

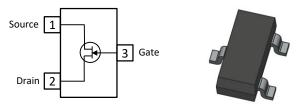
- Low-Noise, High Gain
- Replacement for Japanese 2SK152

Description

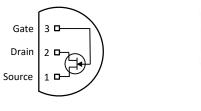
The -20V InterFET IFN152 is a low noise high gain replacement for the Japanese 2SK152 JFET. Gate leakages are typically less than 50pA at room temperatures. The TO-18 package is hermetically sealed and suitable for military applications.











Product Summary

Parameters		IFN152 Min	Unit
BV _{GSS}	Gate to Source Breakdown Voltage	-20	V
I _{DSS}	Drain to Source Saturation Current	5	mA
V _{GS(off)}	Gate to Source Cutoff Voltage	-0.5	V
GFS	Forward Transconductance	30 (typ)	mS

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFN152	Through-Hole	TO-18	Bulk
PN152	Through-Hole	TO-92	Bulk
SMP152	Surface Mount	SOT23	Bulk
	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces
SMP152TR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel
IFN152COT	Chip Orientated Tray (COT Waffle Pack)	СОТ	400/Waffle Pack
IFN152CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.







Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
VRGS	Reverse Gate Source and Gate Drain Voltage	-20	V
I_{FG}	Continuous Forward Gate Current	10	mA
PD	Continuous Device Power Dissipation	300	mW
Р	Power Derating	2.8	mW/°C
Τı	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN152		
	Parameters	Conditions	Min	Max	Unit
V(BR)GSS	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1µA	-20		v
IGSS	Gate to Source Reverse Current	V _{GS} = -10V, V _{DS} = 0V		1	nA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	V _{DS} = -10V, I _D = 100nA	-0.5	-2	v
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = OV, V_{DS} = -10V$ (Pulsed)	5	20	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN152	
	Parameters	Conditions	Тур	Unit
G _{FS}	Forward Transconductance	V _{DS} = -10V, V _{GS} = 0V, f = 1kHz	30	mS
Ciss	Input Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz	15	pF
Crss	Reverse Transfer Capacitance	V _{DS} = 10V, I _D = 0A, f = 1MHz	4	pF



Technical

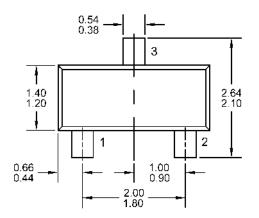
Support

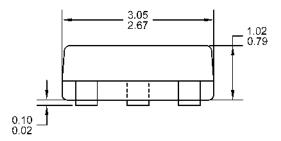
Order

Now

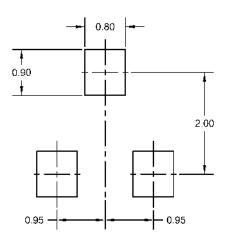
SOT23 (TO-236AB) Mechanical and Layout Data

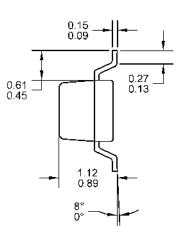
Package Outline Data





Suggested Pad Layout





- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- 5. Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



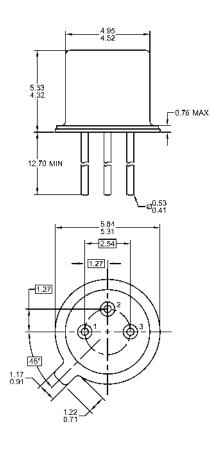


Order

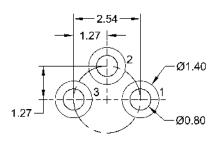
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TO-18 Mechanical and Layout Data

Package Outline Data



Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.29 grams
- 3. Bulk product is shipped in standard ESD shipping material
- 4. Refer to JEDEC standards for additional information.

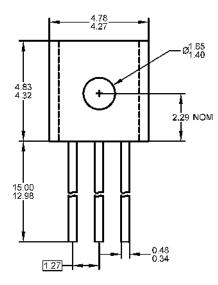
- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.

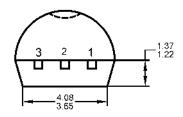




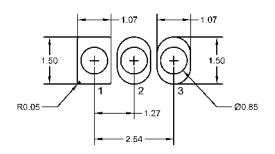
TO-92 Mechanical and Layout Data

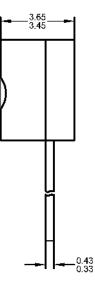
Package Outline Data





Suggested Through-Hole Layout





- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.19 grams
- 3. Molded plastic case UL 94V-0 rated
- 4. Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.